

ABSTRACT

TANTALUM SPUTTERING TARGET

Provided is a tantalum sputtering target containing 1 mass ppm or more and 100 mass ppm or less of tungsten as an essential component, and having a purity of 99.998% or more excluding tungsten and gas components. Additionally provided is a tantalum sputtering target according to according to the above further containing 0 to 100 mass ppm of molybdenum and/or niobium, excluding 0 mass ppm thereof, wherein the total content of tungsten, molybdenum, and niobium is 1 mass ppm or more and 150 mass ppm or less, and wherein the purity is 99.998% or more excluding tungsten, molybdenum, niobium and gas components. Thereby obtained is a high purity tantalum sputtering target comprising a uniform and fine structure and which enables stable plasma and yields superior film evenness (uniformity).